Electronic Version
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Claims

[c1] 1.A method of fabricating an organic light emitting display device, the method comprising:
providing a substrate;
forming an organic light emitting unit on the substrate; and
forming a passivation structure layer including organic and inorganic contents over the organic light emitting unit and the substrate,
wherein the passivation layeris formed by supplying one or more source compound of respective ratio varying in time.

[c2] 2.The method of claim 1 wherein forming the passivation structure is performed by a chemical vapor deposition (CVD) process.

[c3] 3. The method of claim 2, wherein the chemical vapor deposition is a plasma enhanced chemical vapor deposition process.

[c4] 4. The method of claim 1, wherein forming a passivation layer is performed by a sputtering process.

[c5] 5. The method of claim 3, wherein the one or more source compound includes trimethylchlorosilane (TMCS) or hexamethyl disilazane (HMDS).

[c6] 6. The method of claim 4, wherein the one or more source compound includes an organic source compound and an inorganic source compound.

[c7] 7. The method of claim 6, wherein the organic source compound includes PTFE.

[c8] 8. The method of claim 6, wherein the inorganic source compound includes silicon oxide.

[c9] 9. The method of claim 6, wherein the ratio of the organic source compound decreases in time.

[c10] 10. The method of claim 6, wherein the ratio of the inorganic source compound increases in time.

[c11] 11. An organic light emitting display, comprising:
a substrate;
an organic light emitting unit on the substrate, and
a passivation layer covering the organic light emitting unit, wherein the passivation layer is made of a material including organic and inorganic contents varying in the thickness of the passivation layer.

[c12] 12. The organic light emitting display of claim 11,

wherein the organic content is preponderant in a portion of the passivation layer adjacent to the organic light emitting unit.

[c13] 13. The organic light emitting display of claim 11, wherein the inorganic content is preponderant in a portion of the passivation layer not in contact with the organic light emitting unit.

[c14] 14. The organic light emitting display of claim 11, wherein a thickness of the passivation layer is in a range of about 500 to 5000 angstroms.

[c15] 15. The organic light emitting display of claim 11, whereinthe passivation layer includes$SiO_xC_yH_z$, $SiN_xC_yH_z$, or $SiO_wN_xC_yH_z$ compounds.

[c16] 16. The organic light emitting display device of claim 11, wherein the passivation layer has light transmittance in a range of about 40 to 90%.

[c17] 17. An organic light emitting display device formed on a substrate, the organic light emitting display device being fabricated by a process comprising:
forming an organic light emitting unit over the substrate; and
forming a passivation layer including organic and inorganic contents over the organic light emitting unit,

wherein the passivation layer is formed by supplying one or more source compounds of respective ratio varying in time.

[c18] 18. The device of claim 17, wherein forming a passivation layer is performed by a chemical vapor deposition.

[c19] 19. The device of claim 18, wherein the chemical vapor deposition is a plasma enhanced chemical vapor deposition.

[c20] 20. The device of claim 17, wherein forming a passivation layer is performed by a sputtering process.

[c21] 21. The device of claim 19, wherein the one or more source compound includes trimethylchlorosilane (TMCS) or hexamethyl disilazane (HMDS).

[c22] 22. The device of claim 20, wherein the one or more source compound includes an organic source compound and an inorganic source compound.

[c23] 23. The device of claim 22, wherein the organic source compound includes PTFE.

[c24] 24. The device of claim 22, wherein the inorganic source compound includes silicon oxide.

[c25] 25. The device of claim 22, wherein the ratio of the or-

ganic source compound decreases in time.

[c26] 26. The device of claim 22, wherein the ratio of the inorganic source compound increases in time.